N-Channel Enhancement Mode Power MOSFET

Description

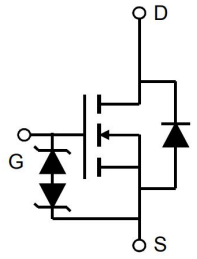
The GT011N03ME uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. It can be used in a wide variety of applications.

General Features

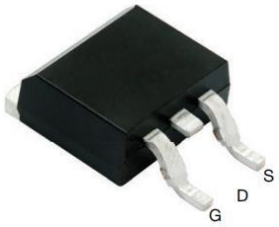
- V_{DS} 30V
- I_D (at V_{GS} = 10V) 209A
- $R_{DS(ON)}$ (at V_{GS} = 10V) < 1.6mΩ
- $R_{DS(ON)}$ (at V_{GS} = 4.5V) < 2.2mΩ
- 100% Avalanche Tested
- RoHS Compliant
- ESD (HBM) : 8KV

Application

- Power switch
- DC/DC converters



Schematic diagram



TO-263

Ordering Information

Device	Package	Marking	Packaging
GT011N03ME	TO-263	GT011N03	800pcs/Reel

Absolute Maximum Ratings T_C = 25ºC, unless otherwise noted

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V_{DS}	30	V
Continuous Drain Current	T_C = 25ºC	I_D	209	A
	T_C = 100ºC		150	
Pulsed Drain Current (note1)		I_{DM}	836	A
Gate-Source Voltage		V_{GS}	±18	V
Power Dissipation		P_D	89	W
Single pulse avalanche energy （note2）		E_{AS}	361	mJ
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 To 175	ºC

Thermal Resistance

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Ambient	R_{thJA}	55	ºC/W
Thermal Resistance, Junction-to-Case	R_{thJC}	1.7	ºC/W

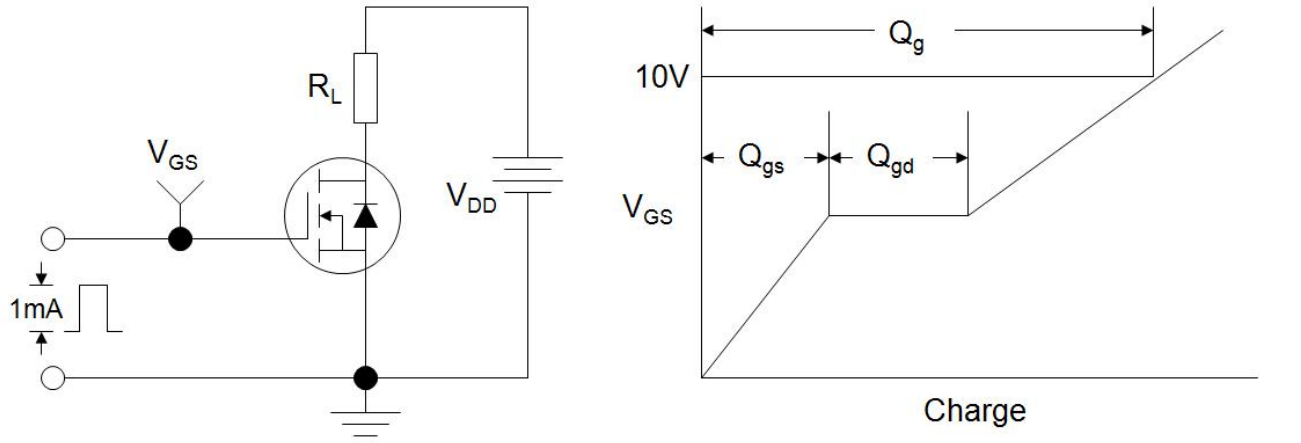
Specifications T_J = 25ºC, unless otherwise noted

Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static Parameters						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	30	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 30V, V_{GS} = 0V	--	--	1	μA
Gate-Source Leakage	I_{GSS}	V_{GS} = ±18V	--	--	±50	uA
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	1.0	1.7	2.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS} = 10V, I_D = 10A	--	1.3	1.6	mΩ
		V_{GS} = 4.5V, I_D = 10A	--	1.8	2.2	
Forward Transconductance	g_{FS}	V_{GS} = 5V, I_D = 10A	--	36	--	S
Dynamic Parameters						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 15V, f = 0.6MHz	--	6000	--	pF
Output Capacitance	C_{oss}		--	2100	--	
Reverse Transfer Capacitance	C_{rss}		--	70	--	
Total Gate Charge	Q_g	V_{DD} = 15V, I_D = 30A, V_{GS} = 10V	--	84	--	nC
Gate-Source Charge	Q_{gs}		--	13	--	
Gate-Drain Charge	Q_{gd}		--	14	--	
Turn-on Delay Time	$t_{d(on)}$	V_{DD} = 15V, I_D = 30A, R_G = 1.6Ω	--	13	--	ns
Turn-on Rise Time	t_r		--	7.5	--	
Turn-off Delay Time	$t_{d(off)}$		--	51	--	
Turn-off Fall Time	t_f		--	8.6	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I_S	T_C = 25ºC	--	--	209	A
Body Diode Voltage	V_{SD}	T_J = 25ºC, I_{SD} = 30A, V_{GS} = 0V	--	--	1.2	V
Reverse Recovery Charge	Qrr	I_F = 30A, V_{GS} = 0V di/dt=100A/us	--	112	--	nC
Reverse Recovery Time	Trr		--	32	--	ns

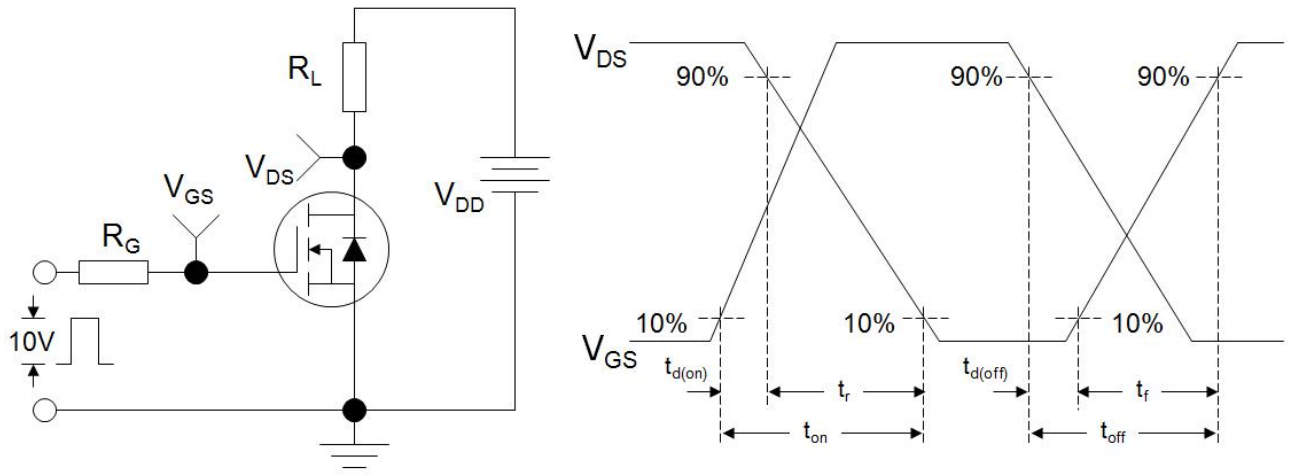
Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. EAS condition : Tj=25℃ ,VDD=30V,VGS=10V,L=0.5mH,Rg=25Ω
   The table shows the minimum avalanche energy, which is 992mJ when the device is tested until failure
3. Identical low side and high side switch with identical R_G

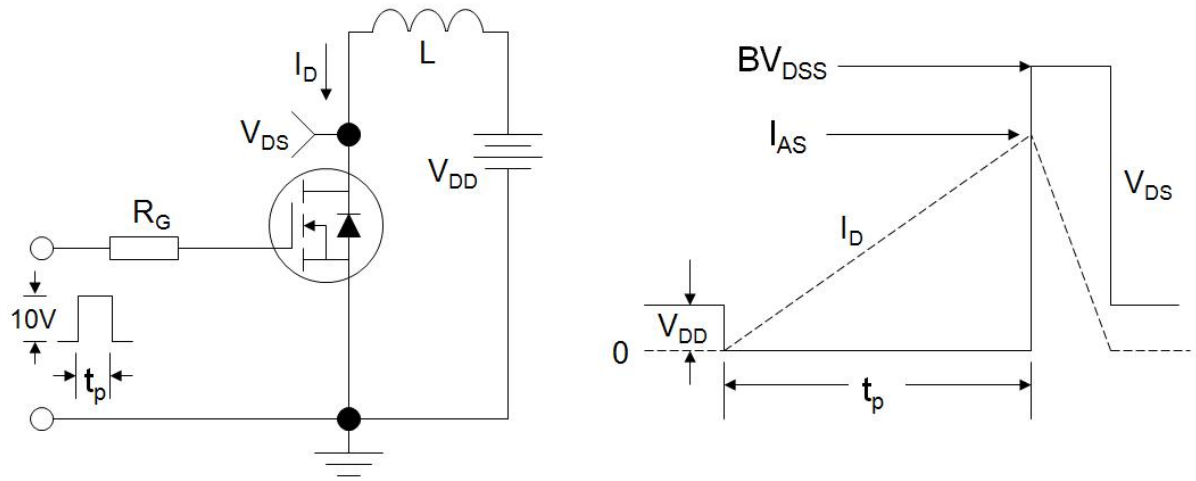
Gate Charge Test Circuit



Switch Time Test Circuit



EAS Test Circuit



Typical Characteristics T_J = 25ºC, unless otherwise noted

Figure 1. Output Characteristics

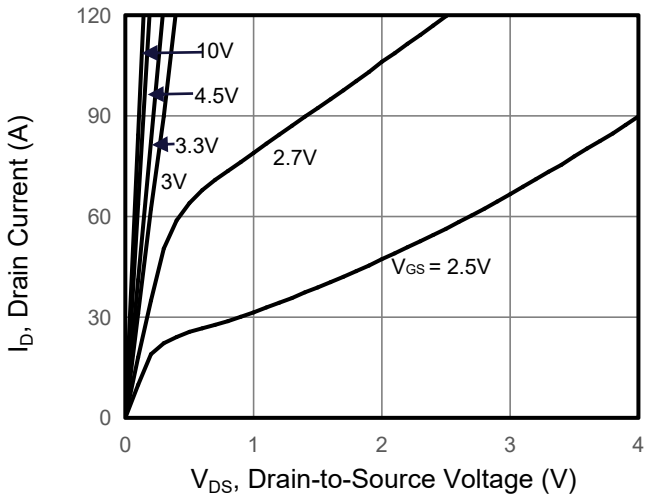


Figure 2. Transfer Characteristics

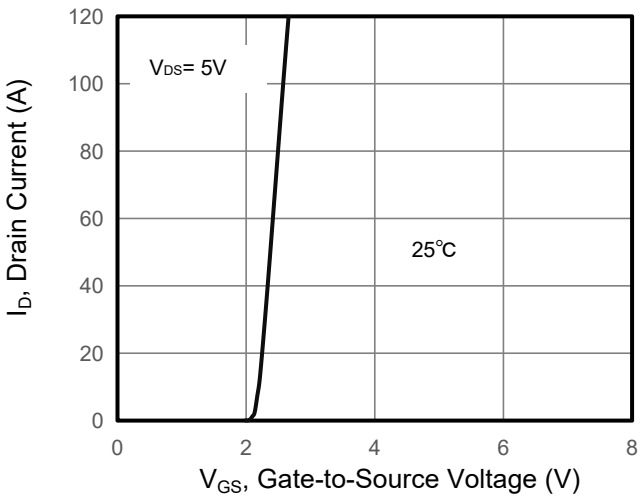


Figure 3. Drain Source On Resistance

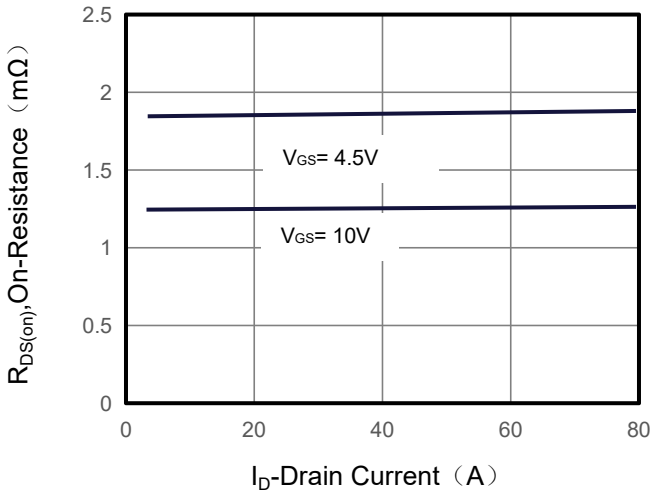


Figure 4. Gate Charge

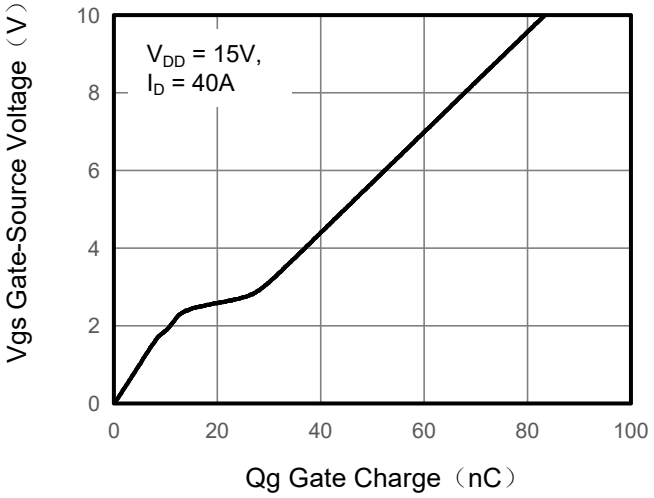


Figure 5. Capacitance

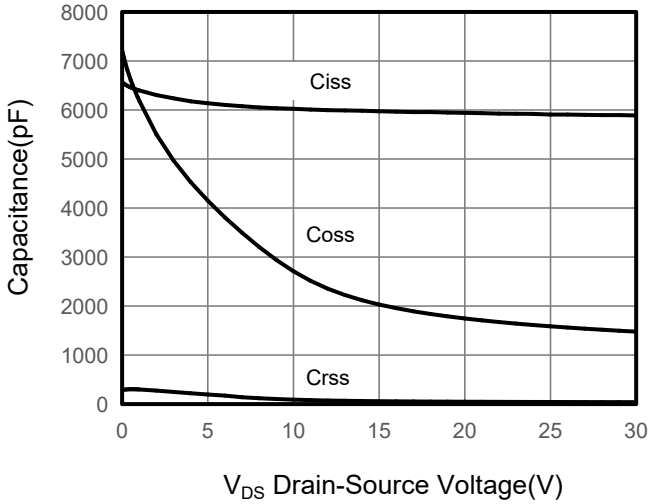
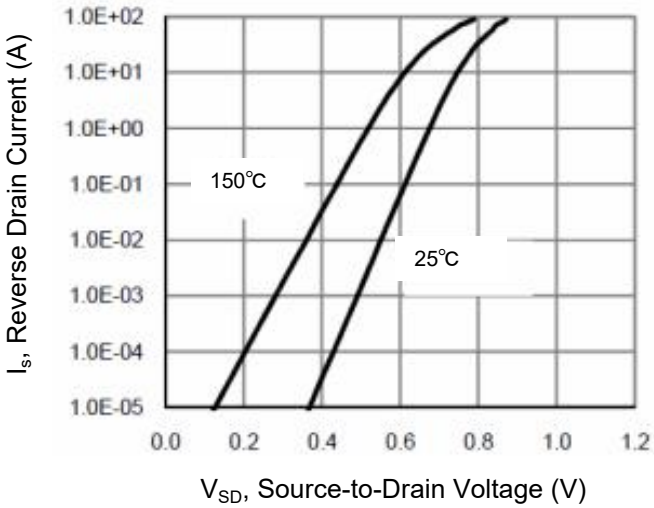


Figure 6. Source-Drain Diode Forward



Typical Characteristics T_J = 25ºC, unless otherwise noted

Figure 7. Drain-Source On-Resistance

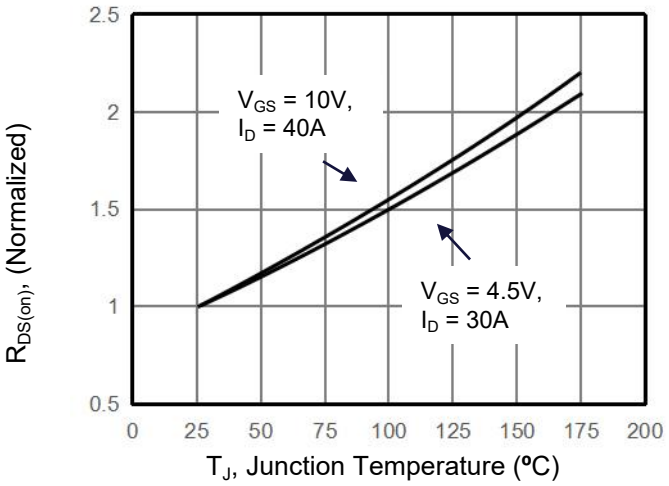


Figure 8. Safe Operation Area

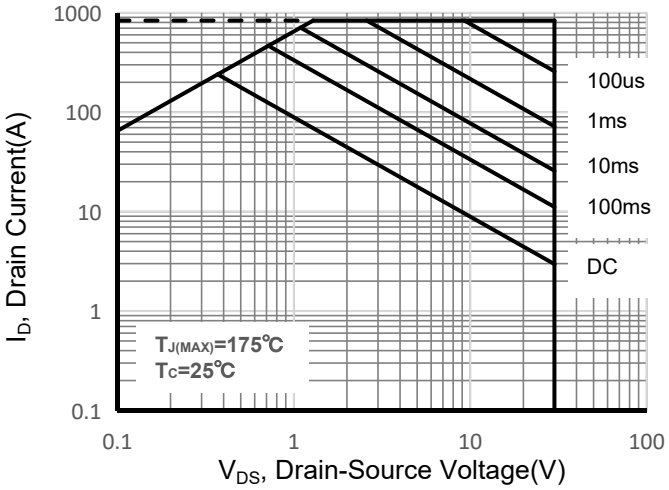


Figure 9. Maximum Continuous Drain Current vs Case Temperature

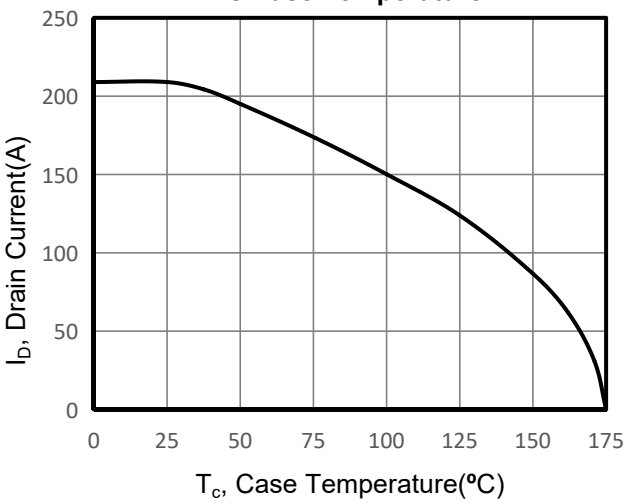
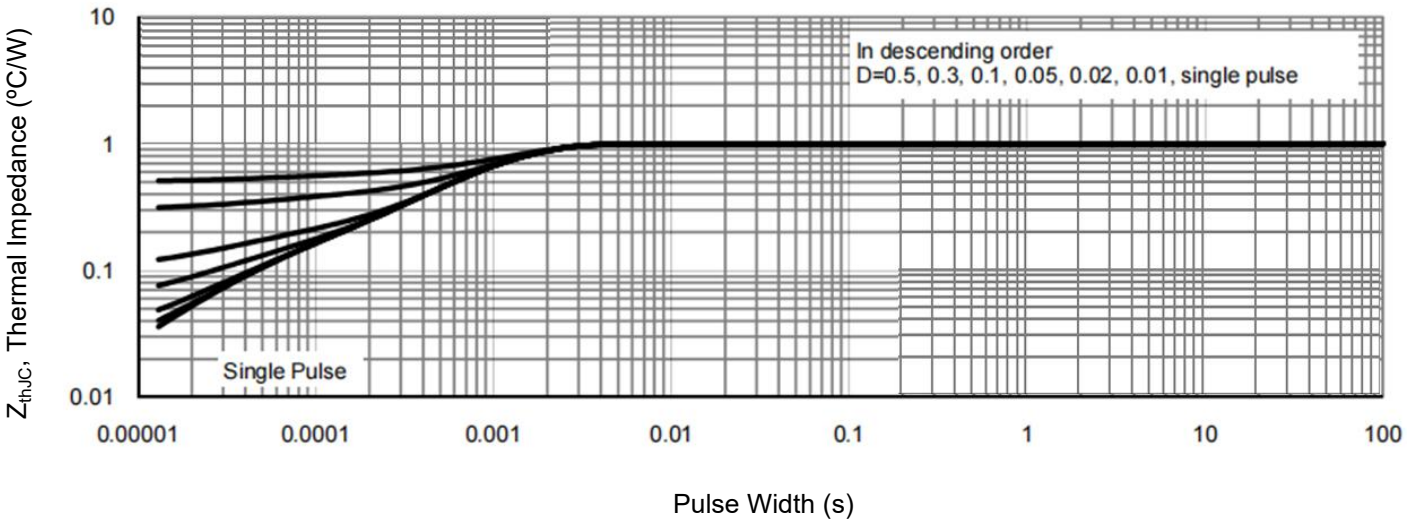
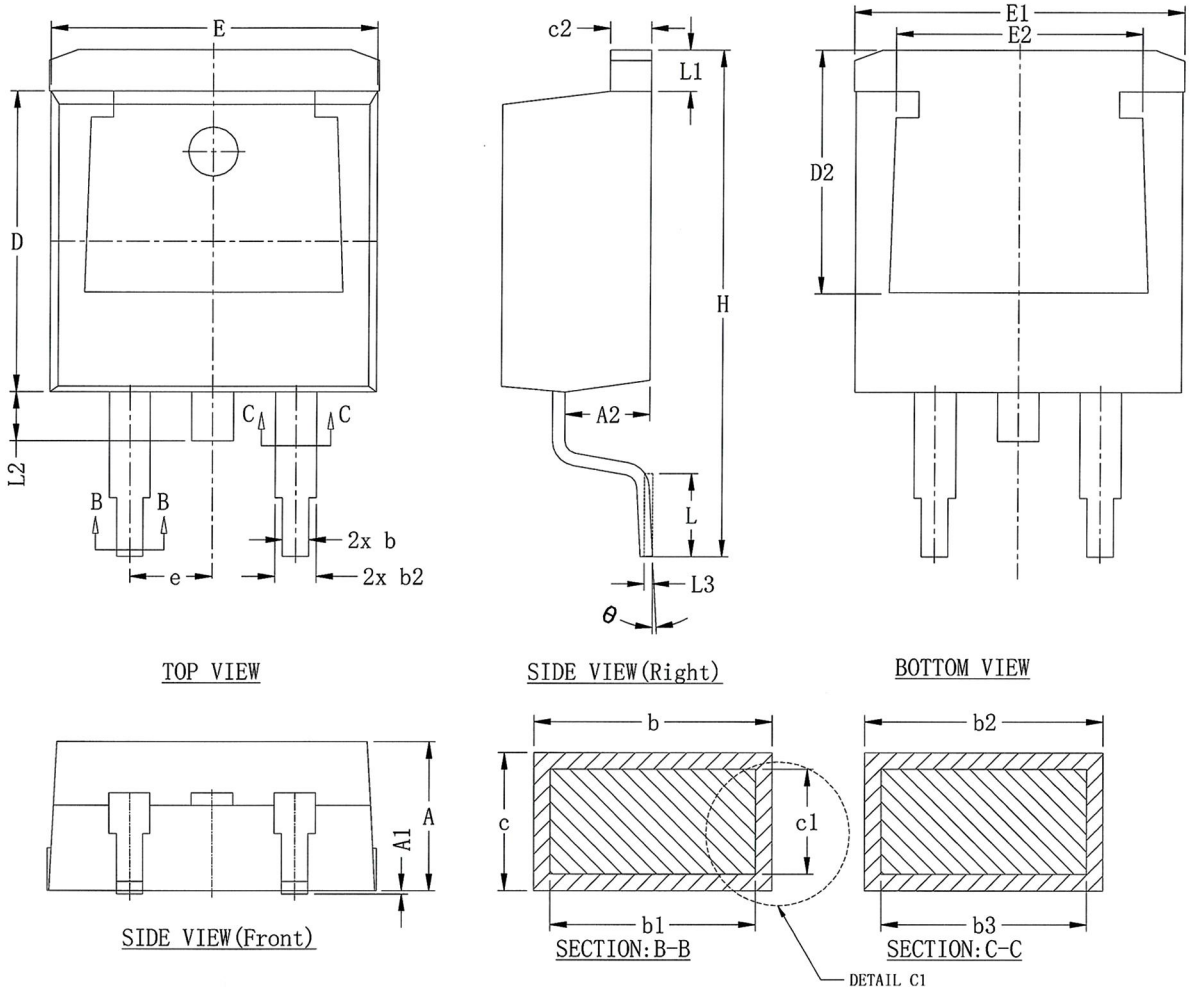


Figure 10. Normalized Maximum Transient Thermal Impedance



TO-263 Package Information



DIM / SYMBOL	MIN.	NOM.	MAX.	DIM / SYMBOL	MIN.	NOM.	MAX.
A	4.450	4.550	4.650	D2	7.215	7.415	7.615
A1	0.000	———	0.150	E	9.900	10.000	10.100
A2	2.500	2.600	2.700	E1	9.900	10.100	10.300
b	0.753	0.853	0.953	E2	7.341	7.541	7.741
b1	0.713	0.813	0.913	e	2.540 BSC.		
b2	1.210	1.310	1.410	H	15.300	15.500	15.700
b3	1.170	1.270	1.370	L	2.340	2.540	2.740
c	0.330	0.421	0.521	L1	1.066	1.266	1.466
c1	0.281	0.381	0.481	L2	1.400	1.500	1.600
c2	1.210	1.310	1.410	L3	0.254 BSC.		
D	9.100	9.200	9.300	θ	0°	---	5°